



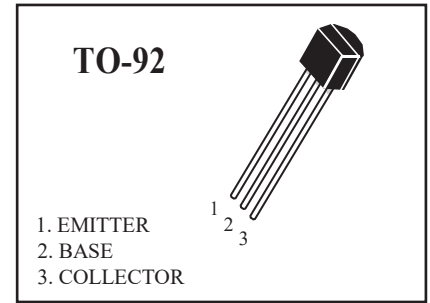
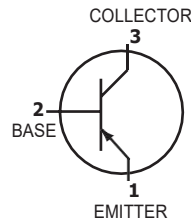
Jiangsu Weida Semiconductor Co., Ltd.

SS8550

Plastic-Encapsulate Transistors

PNP Silicon

Lead(Pb)-Free



ABSOLUTE MAXIMUM RATINGS (Ta=25°C)

Rating	Symbol	SS8550	Unit
Collector-Emitter Voltage	V _{CEO}	-25	V _{dc}
Collector-Base Voltage	V _{CBO}	-40	V _{dc}
Emitter-Base Voltage	V _{EBO}	-5.0	V _{dc}
Collector Current	I _C	-1.5	A _{dc}
Total Device Dissipation T _A =25°C	P _D	1.0	W
Junction Temperature	T _j	150	°C
Storage Temperature	T _{stg}	-55 to +150	°C

DEVICE MARKING

SS8550=SS8550D

ELECTRICAL CHARACTERISTICS

Characteristics	Symbol	Min	Max	Unit
Collector-Emitter Breakdown Voltage ⁽¹⁾ (I _C = -0.1 mA _{dc} , I _B =0)	V _{(BR)CEO}	-25	-	V _{dc}
Collector-Base Breakdown Voltage (I _C = -100 uA _{dc} , I _E =0)	V _{(BR)CBO}	-40	-	V _{dc}
Emitter-Base Breakdown Voltage (I _E = -100 uA _{dc} , I _C =0)	V _{(BR)EBO}	-5.0	-	V _{dc}
Collector Cutoff Current (V _{CB} = -40 V _{dc} , I _E =0 V _{dc})	I _{CBO}	-	-0.1	uA _{dc}
Emitter Cutoff Current (V _{EB} = -5 V _{dc} , I _C =0 V _{dc})	I _{EBO}	-	-0.1	uA _{dc}

1. Pulse Test: Pulse Width ≤ 300 us, Duty Cycle ≤ 2.0%



ELECTRICAL CHARACTERISTICS($T_A=25$ unless otherwise noted) (Continued)

Characteristics	Symbol	Min	TYP	Max	Unit
DC Current Gain ($I_C = -100$ mAdc, $V_{CE} = -1.0$ Vdc)	$h_{FE(1)}$	85	-	400	-
DC Current Gain ($I_C = -800$ mAdc, $V_{CE} = -1.0$ Vdc)	$h_{FE(2)}$	40	-	-	-
Collector-Emitter Saturation Voltage ($I_C = -800$ mAdc, $I_B = -80$ mAdc)	$V_{CE(sat)}$	-	-	-0.5	Vdc
Base-Emitter Saturation Voltage ($I_C = -800$ mAdc, $I_B = -80$ mAdc)	$V_{BE(sat)}$	-	-	-1.2	Vdc
Transition Frequency ($V_{CE} = -10$ V, $I_C = -50$ mA, $f = 30$ MHz)	f_T	100	-	-	MHz

Classification of $h_{FE(1)}$

Rank	B	C	D	E
Range	85-160	120-200	160-300	300-400

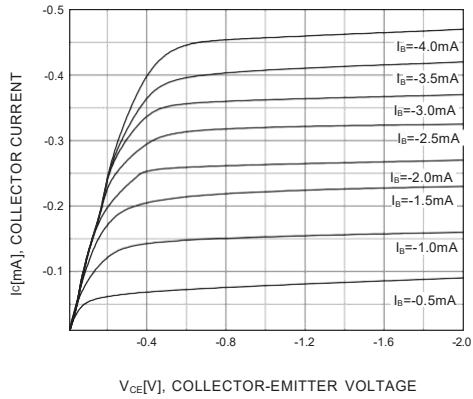


FIG.1 Static Characteristic

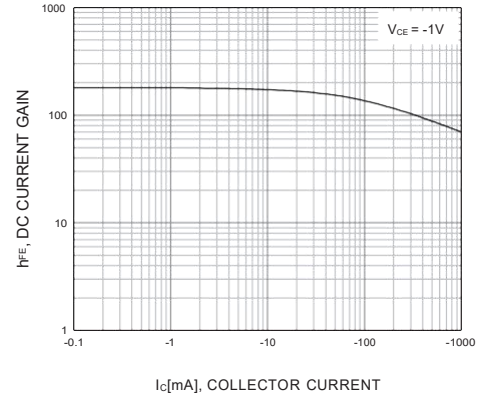


FIG.2 DC Current Gain

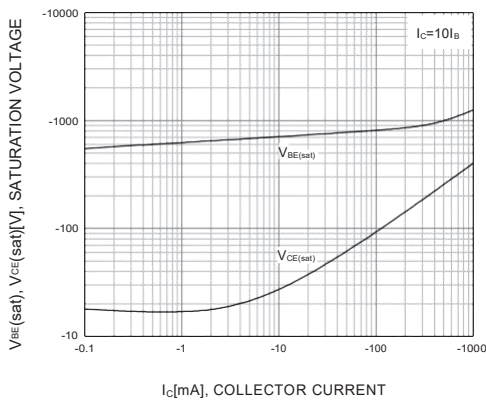


FIG.3 Base-Emitter Saturation Voltage
Collector-Emitter Saturation Voltage

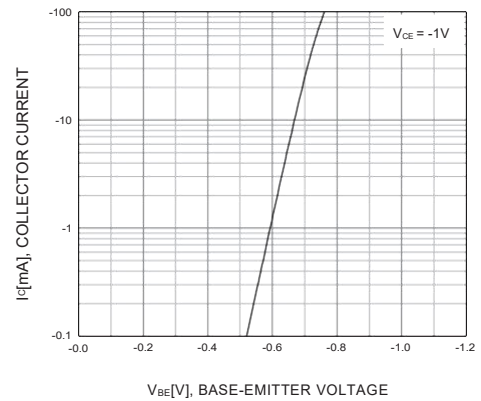


FIG.4 Base-Emitter On Voltage

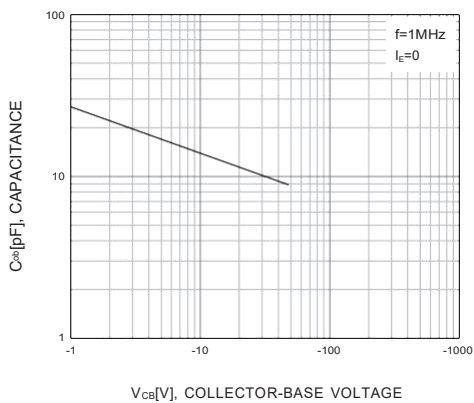


FIG.5 Collector Output Capacitance

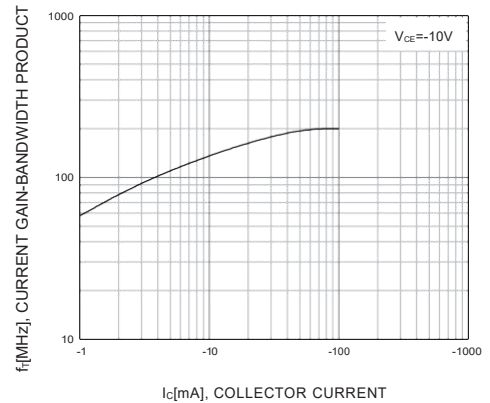
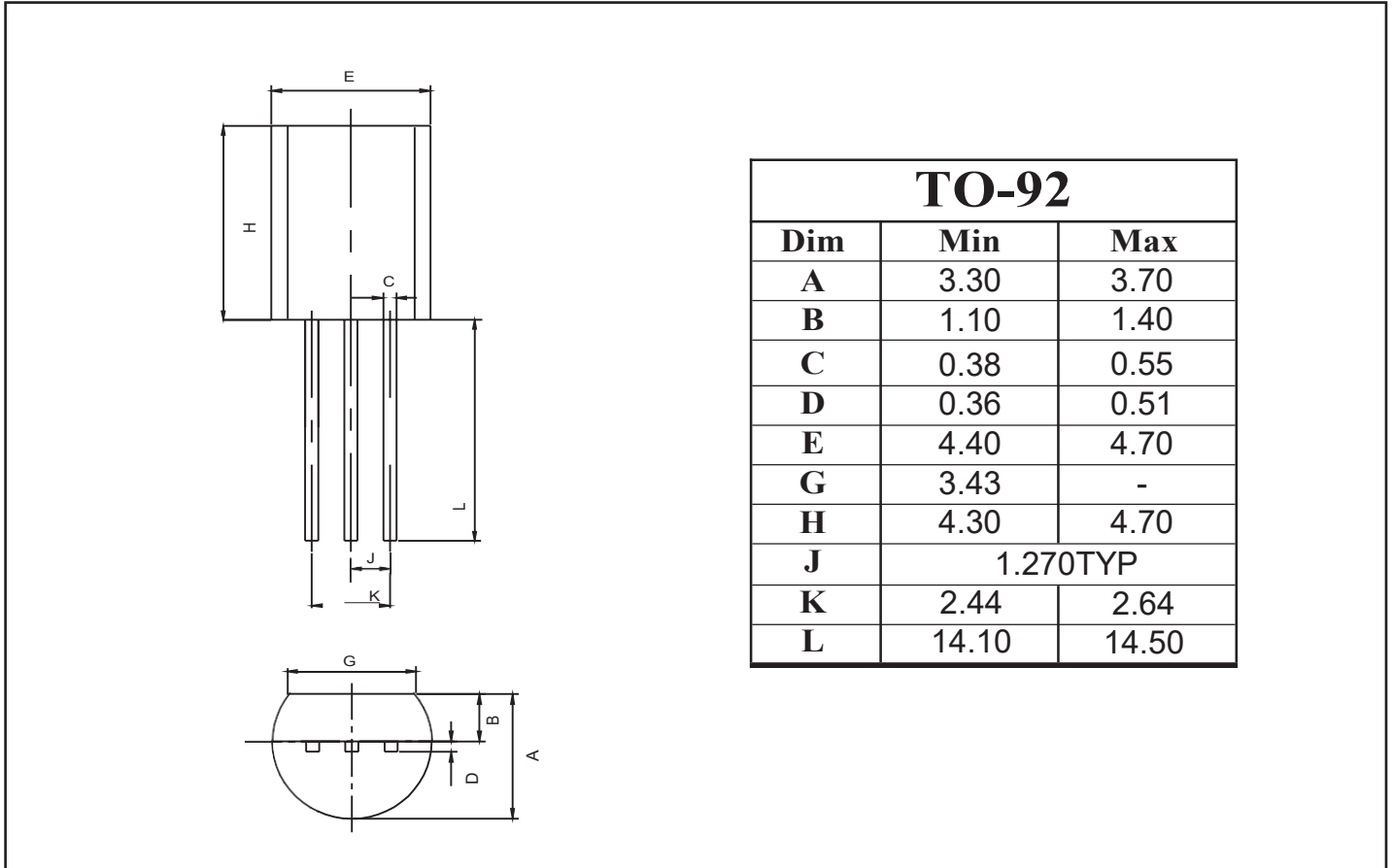


FIG.6 Current Gain Bandwidth Product



TO-92 Outline Dimensions

unit:mm



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